

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising  
a semiconductor substrate, a porous insulating film  
formed above the semiconductor substrate, the porous  
5 insulating film having a relative dielectric constant  
of 2.5 or less and including a first insulating  
material, at least a portion of pores in the porous  
insulating film having on the inner wall thereof  
a layer of a second insulating material which differs  
10 in nature from the first insulating material, and  
a plug and/or a wiring layer buried in the porous  
insulating film.